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CONFIRMATION NO. 7971

Bib Data Sheet

<b>SERIAL NUMBER</b> 10/696,775	<b>FILING OR 371(c) DATE</b> 10/30/2003 <b>RULE</b>	<b>CLASS</b> 438	<b>GROUP ART UNIT</b> 2813	<b>ATTORNEY DOCKET NO.</b> 032076
<b>APPLICANTS</b> Masayuki Furuhashi, Kawasaki, JAPAN; Toshifumi Mori, Kawasaki, JAPAN; Young Suk Kim, Kawasaki, JAPAN; Takayuki Ohba, Kawasaki, JAPAN; Ryou Nakamura, Kawasaki, JAPAN;				
<b>** CONTINUING DATA *****</b> <i>None &amp; W.L.</i>				
<b>** FOREIGN APPLICATIONS *****</b> <i>&amp; W.L.</i> JAPAN 2002-317456 10/31/2002				
<b>IF REQUIRED, FOREIGN FILING LICENSE GRANTED</b> <b>** 02/06/2004</b>				
Foreign Priority claimed <input checked="" type="checkbox"/> yes <input type="checkbox"/> no 35 USC 119 (a-d) conditions <input checked="" type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> Met after met <i>Allowance</i> Verified and Acknowledged <i>S.W.L.</i> Examiner's Signature Initials		<b>STATE OR COUNTRY</b> JAPAN	<b>SHEETS DRAWING</b> 33	<b>TOTAL CLAIMS</b> 25
				<b>INDEPENDENT CLAIMS</b> 6
<b>ADDRESS</b> 38834				
<b>TITLE:</b> 9/16/05 Method for fabricating a semiconductor device including the use of a compound containing silicon and nitrogen to form an insulation film of SiN, SiCN or SiOCN				
<b>FILING FEE RECEIVED</b> 1248	FEES: Authority has been given in Paper No. _____ to charge/credit DEPOSIT ACCOUNT No. _____ for following:		<input type="checkbox"/> All Fees <input type="checkbox"/> 1.16 Fees ( Filing ) <input type="checkbox"/> 1.17 Fees ( Processing Ext. of time ) <input type="checkbox"/> 1.18 Fees ( Issue ) <input type="checkbox"/> Other _____ <input type="checkbox"/> Credit	